# **GL496**

# **High Speed Infrared Emitting Diode**

#### **■** Features

1. High speed response (response frequency: 40MHz)

2. Peak emission wavelength λp: TYP. 880 mm

3. Half intensity angle  $\Delta\theta$ :  $\pm 22^{\circ}$ 

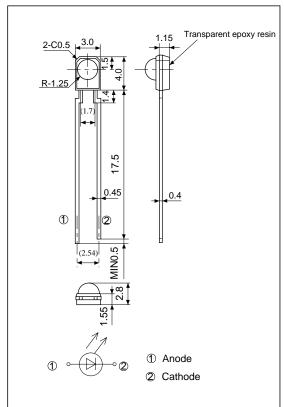
4. Lead bending type may be used.

## **■** Applications

- 1. AV equipment
- 2. Personal computers
- 3. Portable information terminal equipment

#### **■** Outline Dimensions





### ■ Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit	
Forward current	$I_F$	50	mA	
*1Peak forward current	$I_{FM}$	0.5	A	
Reverse voltage	VR	4	V	
Power dissipation	P	87.5	mW	
Operating temperature	Topr	- 25 to + 85	°C	
Storage temperature	T <sub>stg</sub>	- 40 to + 90	°C	
*2 Soldering temperature	T <sub>sol</sub>	260	°C	

<sup>\*1</sup> Pulse width 100 µ s, Duty ratio=0.01

<sup>\*2</sup> For MAX. 5 seconds at the position of 1.4 mm from the resin edge



### **■** Electro-optical Characteristics

(Ta=25 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage	VF	$I_F = 50 \text{mA}$	-	1.55	1.75	V
Peak forward voltage	$V_{\text{FM}}$	$I_{FM} = 0.5A$	-	2.6	3.6	V
Reverse current	$I_R$	$V_R = 3V$	-	-	10	μΑ
*3 Radiant intensity	$I_{\rm E}$	$I_F = 50 \text{mA}$	3.0	10.0	-	mW/sr
Radiant flux	$\Phi_{\rm E}$	$I_F = 50 \text{mA}$	-	12	-	mW
Peak emission wavelength	$\lambda_p$	$I_F = 50 \text{mA}$	850	880	900	nm
Half intensity wavelength	Δλ	$I_F = 50 \text{mA}$	-	50	-	nm
Terminal capacitance	Ct	$V_R = 0V, f = 1MHz$	-	60	-	pF
*4 Response frequency	fc	$I_F = 50mA + 10mAp-p$	-	40	-	MHz
Half intensity angle	Δθ	$I_F = 50 \text{mA}$	-	± 22	-	۰

<sup>\*3</sup> Value obtained by converting the value in power of radiant fluxes emitted at the solid angle of 0.01 sr (steradian) in the direction of mechanical axis of the lens portion into 1 sr or all those emitted from the light emitting diode.

Fig. 1 Forward Current vs. Ambient

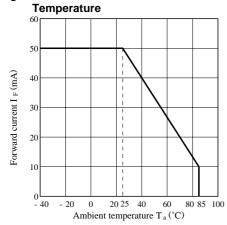
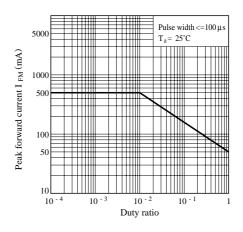


Fig. 2 Peak Forward Current vs. Duty Ratio



<sup>\*4</sup> Frequency to bring about -3dB reduction of modulated radiant intensity from 100kHz

Fig. 3 Spectral Distribution

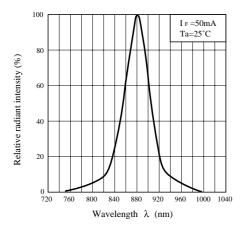


Fig. 5 Forward Current vs. Forward Voltage

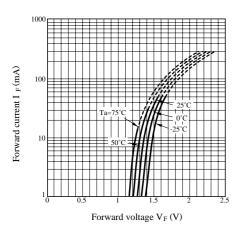


Fig. 7 Radiant Intensity vs. Forward Current

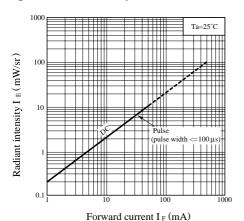


Fig. 4 Peak Emission Wavelength vs.
Ambient Temperature

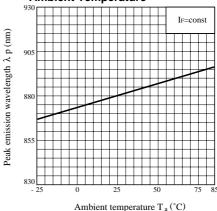


Fig. 6 Relative Radiant Flux vs. Ambient Temperature

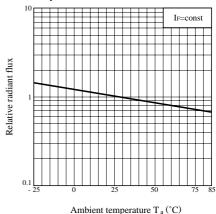
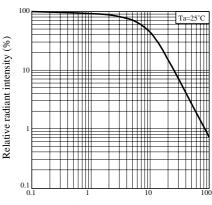


Fig. 8 Relative Radiant Intensity vs. Distance



Distance to detector (mm)

Fig. 9 Relative Radiant Intensity vs. Frequency

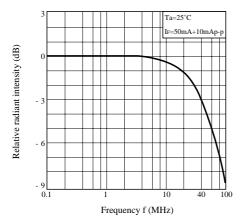
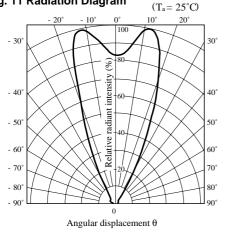
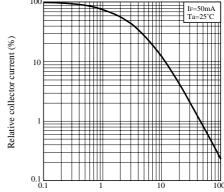


Fig. 11 Radiation Diagram



• Please refer to the chapter "Precautions for Use". (Page 78 to 93)

Fig. 10 Relative Collector Current vs. Distance (Detector: PT414PI)



Distance between emitter and detector d (mm)

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  - Gas leakage sensor breakers
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